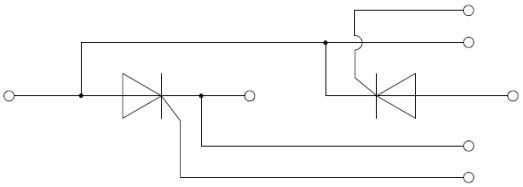
DG 1 E 0

bslcmi l Gi of

nol m

J l g n l	P fo	Ohcn
℃		

fc nci hm



mi fon G r cg og L ncham

J l g n l	i h cnci hm	Msg i f	P fo m	Ohcn
	℃			
				℃
				℃

f nlc f b l n lcmncm

J l g n l	i h cnc hm	Msg i f	P fo m			Ohcn
			Gch(	s (	G r (	
	℃					
	℃					
	℃					
	℃					

℃

l l lcha Ch i lg nch h

pc	G lecha	J e a	cabn	Chh l i r	J l lri h

s c f f nlc f b lg f b l n lcmcm

FIG.1: Power dissipation vs. on-state current

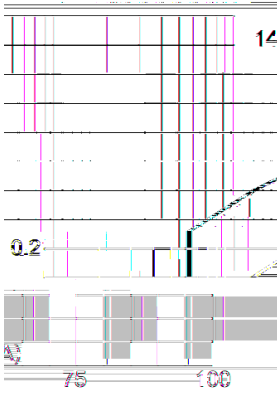


FIG.2: Maximum transient thermal impedance

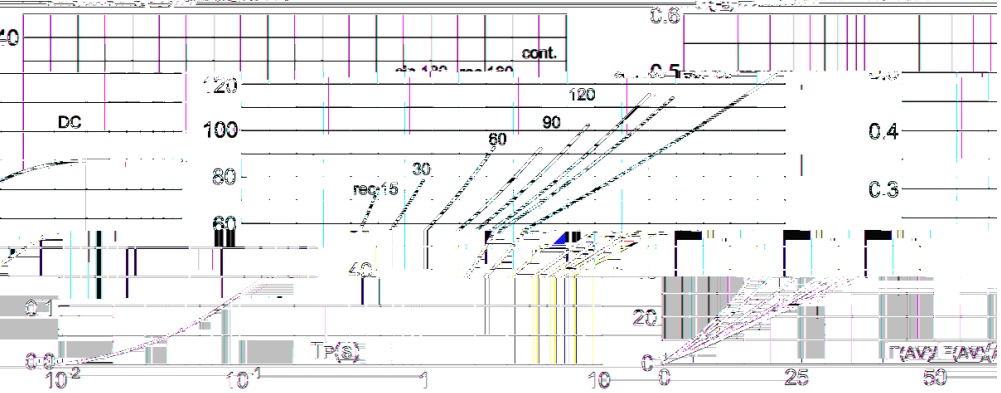


FIG.3: Forward characteristics

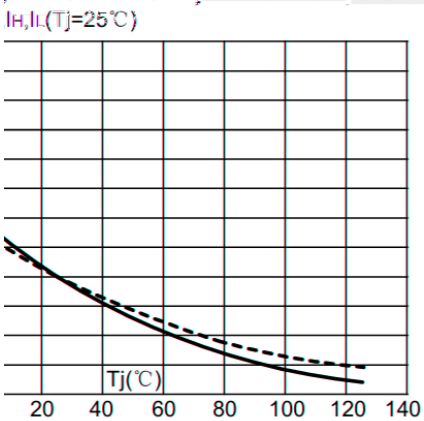
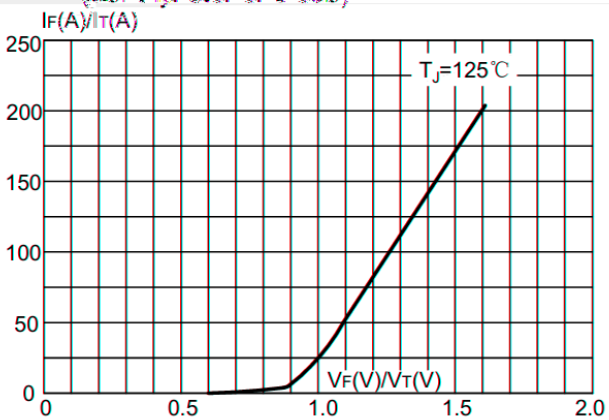


FIG.4: Relative variations of gate trigger current, holding current versus junction temperature



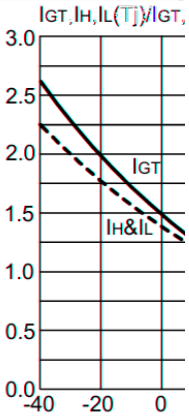
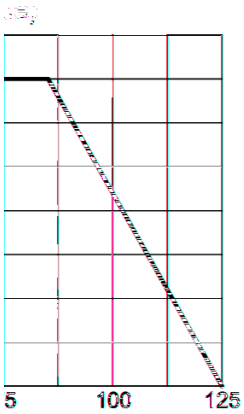


FIG.5 Gate trigger characteristics



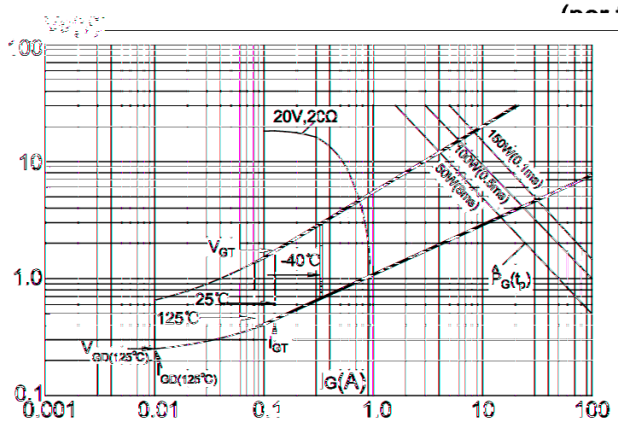
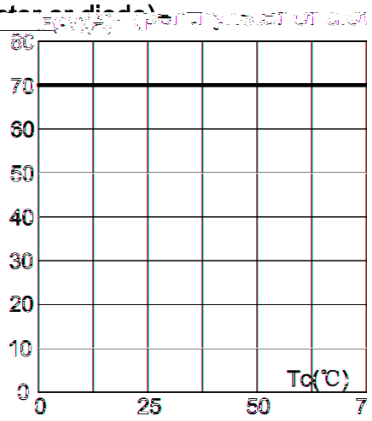
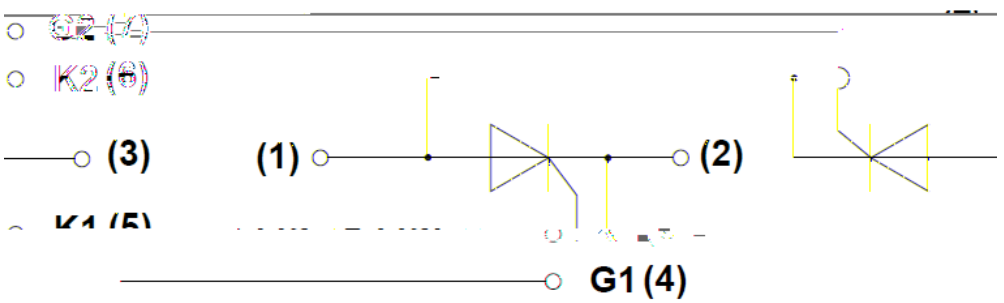
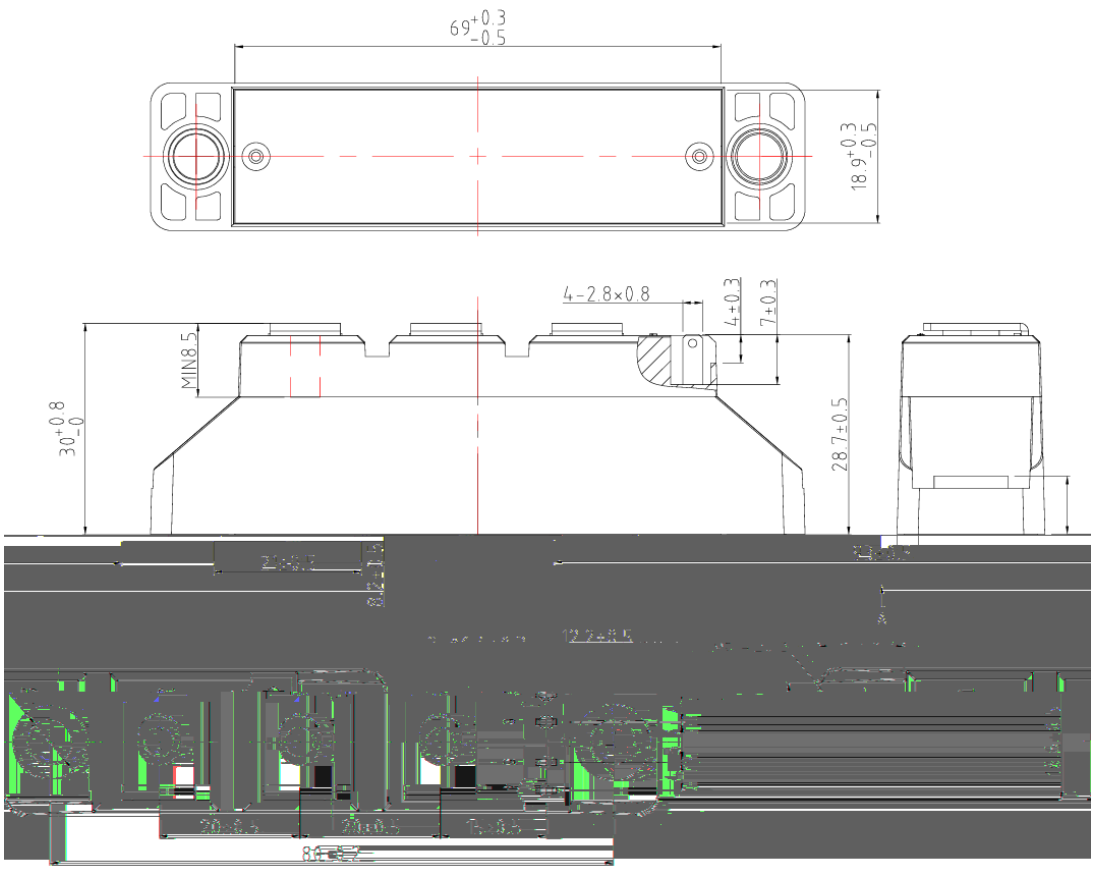


FIG.6: Forward current vs. case temperature (per thyristor or diode)



d oon c al g



J e a l onfch m"g g